Seiya Kasai

List of Publications by Year
in descending order

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142	1,432	393982	476904
papers	citations	19 h-index	29 g-index

144	144	144	1066
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Mechanism of surface conduction in the vicinity of Schottky gates on AlGaNâ•GaN heterostructures. Applied Physics Letters, 2007, 91, .	1.5	86
2	Hexagonal binary decision diagram quantum logic circuits using Schottky in-plane and wrap-gate control of GaAs and InGaAs nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 11, 149-154.	1.3	63
3	Stochastic Resonance in Schottky Wrap Gate-controlled GaAs Nanowire Field-Effect Transistors and Their Networks. Applied Physics Express, 0, 1, 083001.	1.1	61
4	Fabrication and Characterization of GaAs Single Electron Devices Having Single and Multiple Dots Based on Schottky In-Plane-Gate and Wrap-Gate Control of Two-Dimensional Electron Gas. Japanese Journal of Applied Physics, 1997, 36, 1678-1685.	0.8	58
5	Silicon nanowire-array-textured solar cells for photovoltaic application. Journal of Applied Physics, 2010, 108, 094318.	1.1	56
6	Threshold-variation-enhanced adaptability of response in a nanowire field-effect transistor network. Applied Physics Letters, 2010, 96, .	1.5	36
7	Nearly Temperature-Independent Saturation Drain Current in a Multi-Mesa-Channel AlGaN/GaN High Electron Mobility Transistor. Applied Physics Express, 0, 1, 023001.	1.1	33
8	Amoeba-inspired nanoarchitectonic computing implemented using electrical Brownian ratchets. Nanotechnology, 2015, 26, 234001.	1.3	31
9	Fabrication of GaAs-based integrated half and full adders by novel hexagonal BDD quantum circuit approach. Solid-State Electronics, 2003, 47, 199-204.	0.8	29
10	Enhancement of weak-signal response based on stochastic resonance in carbon nanotube field-effect transistors. Journal of Applied Physics, 2010, 108, .	1.1	29
11	Novel Hybrid Voltage Controlled Ring Oscillators Using Single Electron and MOS Transistors. IEEE Nanotechnology Magazine, 2007, 6, 146-157.	1.1	28
12	Effects of gap states on scanning tunneling spectra observed on (110)- and (001)-oriented clean surfaces and ultrathin Si layer covered surfaces of GaAs prepared by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2100.	1.6	27
13	Unpinning of Fermi level in nanometer-sized Schottky contacts on GaAs and InP. Applied Surface Science, 2000, 166, 92-96.	3.1	25
14	Current transport and capacitanceâ€“voltage characteristics of GaAs and InP nanometer-sized Schottky contacts formed by in situ electrochemical process. Applied Surface Science, 2001, 175-176, 181-186.	3.1	25
15	Room-temperature discrete-charge-fluctuation dynamics of a single molecule adsorbed on a carbon nanotube. Nanoscale, 2017, 9, 10674-10683.	2.8	25
16	Electron Beam Induced Current Characterization of Novel GaAs Quantum Nanostructures Based on Potential Modulation of Two-Dimensional Electron Gas by Schottky In-Plane Gates. Japanese Journal of Applied Physics, 1996, 35, 6652-6658.	0.8	24
17	Observation of first and third harmonic responses in two-dimensional AlGaAs/GaAs HEMT devices due to plasma wave interaction. Superlattices and Microstructures, 2008, 44, 754-760.	1.4	23
18	Room temperature nonlinear operation of a graphene-based three-branch nanojunction device with chemical doping. Applied Physics Letters, 2012, 100, .	1.5	22

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19	Control of GaAs Schottky Barrier Height by Ultrathin Molecular beam epitaxy si interface control layer. Japanese Journal of Applied Physics, 1993, 32, 502-510.	0.8	21
20	Quantum-Dot Logic Circuits Based on the Shared Binary-Decision Diagram. Japanese Journal of Applied Physics, 2001, 40, 4485-4488.	0.8	21
21	Electrode-contact enhancement in silicon nanowire-array-textured solar cells. Applied Physics Letters, 2011, 98, 143108.	1.5	21
22	Method for Controlling Electrical Properties of Single-Layer Graphene Nanoribbons via Adsorbed Planar Molecular Nanoparticles. Scientific Reports, 2015, 5, 12341.	1.6	21
23	Dynamics and control of recombination process at semiconductor surfaces, interfaces and nano-structures. Solar Energy, 2006, 80, 629-644.	2.9	20
24	Fabrication and characterization of a GaAs-based three-terminal nanowire junction device controlled by double Schottky wrap gates. Applied Physics Letters, 2007, 90, 102104.	1.5	19
25	0.86 eV Platinum Schottky Barrier on Indium Phosphide by In Situ Electrochemical Process and Its Application to MESFETs. Japanese Journal of Applied Physics, 1996, 35, 1258-1263.	0.8	18
26	Gate control characteristics in GaAs nanometer-scale Schottky wrap gate structures. Applied Surface Science, 2002, 190, 242-246.	3.1	18
27	Effect of Size Reduction on Switching Characteristics in GaAs-Based Schottky-Wrap-Gate Quantum Wire Transistors. Japanese Journal of Applied Physics, 2008, 47, 3086-3090.	0.8	18
28	Lateral tunneling injection and peripheral dynamic charging in nanometer-scale Schottky gates on AlGaN/GaN hetrosturucture transistors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1799.	1.6	17
29	Amoeba-inspired computing architecture implemented using charge dynamics in parallel capacitance network. Applied Physics Letters, 2013, 103, 163703.	1.5	17
30	GaAs-Based Nanowire Devices with Multiple Asymmetric Gates for Electrical Brownian Ratchets. Japanese Journal of Applied Physics, 2013, 52, 06GE07.	0.8	16
31	A binary-decision-diagram-based two-bit arithmetic logic unit on a GaAs-based regular nanowire network with hexagonal topology. Nanotechnology, 2009, 20, 245203.	1.3	15
32	Intrinsic charge carrier mobility in single-crystal OFET by â€œfast trapping vs. slow detrappingâ€•model. Organic Electronics, 2018, 54, 237-244.	1.4	15
33	Fabrication of AlGaN/GaN Quantum Nanostructures by Methane-Based Dry Etching and Characterization of Their Electrical Properties. Japanese Journal of Applied Physics, 2003, 42, 2375-2381.	0.8	14
34	Basic Control Characteristics of Novel Schottky In-Plane and Wrap Gate Structures Studied by Simulation and Transport Measurements in GaAs and InGaAs Quantum Wires. Japanese Journal of Applied Physics, 1997, 36, 4156-4160.	0.8	13
35	Electrical Properties of Nanometer-Sized Schottky Contacts on n-GaAs and n-InP Formed byin SituElectrochemical Process. Japanese Journal of Applied Physics, 2000, 39, 4609-4615.	0.8	13
36	Gate control, surface leakage currents, and peripheral charging in AlGaN/GaN heterostructure field effect transistors having nanometer-scale schottky gates. Journal of Electronic Materials, 2006, 35, 568-575.	1.0	13

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37	Study on Nonlinear Electrical Characteristics of GaAs-Based Three-Branch Nanowire Junctions Controlled by Schottky Wrap Gates. Japanese Journal of Applied Physics, 2008, 47, 4958-4964.	0.8	13
38	Characterization of Low-Frequency Noise in Etched GaAs Nanowire Field-Effect Transistors Having SiN$_{x}$ Gate Insulator. Japanese Journal of Applied Physics, 2012, 51, 06FE18.	0.8	13
39	Novel Quantum Wire Branch-Switches for Binary Decision Diagram Logic Architecture Utilizing Schottky Wrap-Gate Control of GaAs/AlGaAs Nanowires. Japanese Journal of Applied Physics, 2002, 41, 2671-2674.	0.8	12
40	Boolean Logic Gates Utilizing GaAs Three-Branch Nanowire Junctions Controlled by Schottky Wrap Gates. Japanese Journal of Applied Physics, 2009, 48, 06FD01.	0.8	12
41	Compact Reconfigurable Binary-Decision-Diagram Logic Circuit on a GaAs Nanowire Network. Applied Physics Express, 2010, 3, 025002.	1.1	12
42	Electrical Properties of Nanometer-Sized Schottky Contacts for Gate Control of IIIâ€“V Single Electron Devices and Quantum Devices. Japanese Journal of Applied Physics, 2001, 40, 2021-2025.	0.8	11
43	Reactive Ion Beam Etching of GaN and AlGaN/GaN for Nanostructure Fabrication Using Methane-Based Gas Mixtures. Japanese Journal of Applied Physics, 2002, 41, 2689-2693.	0.8	11
44	Device interference in GaAs quantum wire transistors and its suppression by surface passivation using Si interface control layer. Journal of Vacuum Science & Technology B, 2006, 24, 2060.	1.3	11
45	Silicon nanostructure solar cells with excellent photon harvesting. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 021014.	0.6	11
46	Rectification Effects of ZnO-Based Transparent Nanodiodes on Glass and Flexible Plastic Substrates. Japanese Journal of Applied Physics, 2013, 52, 06GE09.	0.8	11
47	GaAs and InGaAs single electron hexagonal nanowire circuits based on binary decision diagram logic architecture. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 925-929.	1.3	10
48	Graph-based quantum logic circuits and their realization by novel GaAs multiple quantum wire branch switches utilizing Schottky wrap gates. Microelectronic Engineering, 2002, 63, 287-291.	1.1	10
49	Large Modulation of Conductance in Interdigital-Gated HEMT Devices Due to Surface Plasma Wave Interactions. Japanese Journal of Applied Physics, 2005, 44, 2729-2734.	0.8	10
50	Insight into in-plane isotropic transport in anthracene-based organic semiconductors. Journal of Materials Chemistry C, 2019, 7, 14275-14283.	2.7	10
51	Effects of surface states on control characteristics of nano-meter scale Schottky gates formed on GaAs. Solid-State Electronics, 2003, 47, 323-331.	0.8	9
52	Investigation on Stochastic Resonance in Quantum Dot and Its Summing Network. International Journal of Nanotechnology and Molecular Computation, 2009, 1, 70-79.	0.3	9
53	Multipath-switching device utilizing a GaAs-based multiterminal nanowire junction with size-controlled dual Schottky wrap gates. Applied Physics Letters, 2007, 90, 203504.	1.5	8
54	Novel structure of GaAs-based interdigital-gated HEMT plasma devices for solid-state THz wave amplifier. Microelectronics Journal, 2007, 38, 1268-1272.	1.1	8

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55	Control of stochastic resonance response in a GaAsâ€based nanowire fieldâ€effect transistor. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 384-386.	0.8	8
56	Design and characterization of nonlinear functions for the transmission of a small signal with non-Gaussian noise. Physical Review E, 2013, 88, 062127.	0.8	8
57	Detection of molecular charge dynamics through current noise in a GaAs-based nanowire FET. Japanese Journal of Applied Physics, 2015, 54, 04DN07.	0.8	8
58	Concept, analysis, and demonstration of a novel delay network exhibiting stochastic resonance induced by external noise. , 2015, 37, 1-12.		8
59	Design Framework of Image Sensor System Based on Dynamic Range Extension by Adding Noise for Saturated Conditions. IEEE Transactions on Systems, Man, and Cybernetics: Systems, 2016, 46, 1121-1128.	5.9	8
60	Divergence of relative difference in Gaussian distribution function and stochastic resonance in a bistable system with frictionless state transition. Applied Physics Express, 2018, 11, 037301.	1.1	8
61	Amoeba-inspired analog electronic computing system integrating resistance crossbar for solving the travelling salesman problem. Scientific Reports, 2020, 10, 20772.	1.6	8
62	Schottky Wrap Gate Control of Semiconductor Nanowire Networks for Novel Quantum Nanodevice-Integrated Logic Circuits Utilizing BDD Architecture. Journal of Computational and Theoretical Nanoscience, 2007, 4, 1120-1132.	0.4	8
63	Characterization of Low-Frequency Noise in Etched GaAs Nanowire Field-Effect Transistors Having SiNxGate Insulator. Japanese Journal of Applied Physics, 2012, 51, 06FE18.	0.8	8
64	Integration of interdigital-gated plasma wave device for proximity communication system application. Microelectronics Journal, 2007, 38, 1263-1267.	1.1	7
65	Energy gap opening by crossing drop cast single-layer graphene nanoribbons. Nanotechnology, 2018, 29, 315705.	1.3	7
66	Conductance gap anomaly in scanning tunneling spectra of MBE-Grown (0 0 1) surfaces of IIIâ€“V compound semiconductors. Applied Surface Science, 2001, 175-176, 255-259.	3.1	6
67	Stochastic resonance among single-electron neurons on Schottky wrap-gate device. International Congress Series, 2006, 1291, 213-216.	0.2	6
68	Grapheneâ€based threeâ€branch nanoâ€junction (TBJ) logic inverter. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1485-1488.	0.8	6
69	Detection of weak biological signal utilizing stochastic resonance in a GaAs-based nanowire FET and its parallel summing network. Japanese Journal of Applied Physics, 2014, 53, 06JE01.	0.8	6
70	Characterization of Low-Frequency Noise in GaAs Nanowire Field-Effect Transistors Controlled by Schottky Wrap Gate. Japanese Journal of Applied Physics, 2011, 50, 06GF18.	0.8	6
71	GaAs-Based Single Electron Transistors and Logic Inverters Utilizing Schottky Wrap-Gate Controlled Quantum Wires and Dots. Japanese Journal of Applied Physics, 2001, 40, 2029-2032.	0.8	5
72	Tunneling Injection of Electrons at Nanometer-Scale Schottky Gate Edge of AlGaN/GaN Heterostructure Transistors and Its Computer Simulation. E-Journal of Surface Science and Nanotechnology, 2005, 3, 433-438.	0.1	5

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73	TOWARD ULTRA-LOW POWER III-V QUANTUM LARGE SCALE INTEGRATED CIRCUITS FOR UBIQUITOUS NETWORK ERA. International Journal of High Speed Electronics and Systems, 2006, 16, 421-436.	0.3	5
74	Multiple-Valued Logic Gates Using Asymmetric Single-Electron Transistors. , 2009, , .		5
75	Voltage Transfer Characteristics in GaAs-Based Three-Branch Nanowire Junctions Controlled by Schottky Wrap Gates. Japanese Journal of Applied Physics, 2010, 49, 06GG03.	0.8	5
76	Programmable nano-switch array using SiN/GaAs interface traps on a GaAs nanowire network for reconfigurable BDD logic circuits. Microelectronic Engineering, 2011, 88, 2755-2758.	1.1	5
77	Structural parameter dependence of directed current generation in GaAs nanowire-based electron Brownian ratchet devices. Japanese Journal of Applied Physics, 2015, 54, 06FG02.	0.8	5
78	Novel Nanowire-Based Flip-Flop Circuit Utilizing Gate-Controlled GaAs Three-Branch Nanowire Junctions. Japanese Journal of Applied Physics, 2011, 50, 06GF03.	0.8	5
79	Identification of Graphene Layer Numbers from Color Combination Contrast Image for Wide-Area Characterization. Japanese Journal of Applied Physics, 2012, 51, 06FD09.	0.8	5
80	Fabrication and Characterization of Novel Lateral Surface Superlattice Structure Utilizing Schottky Barrier Height Control by Doped Silicon Interface Control Layers. Japanese Journal of Applied Physics, 1996, 35, 1340-1347.	0.8	4
81	Scanned-probe topological and spectroscopic study of surface states on clean and Si-deposited GaAs (001)-c(4Ã—4) surfaces. Applied Surface Science, 2002, 190, 269-274.	3.1	4
82	Control of Order Parameter during Growth of In0.5Ga0.5P/GaAs Heterostructures by Gas Source Molecular Beam Epitaxy Using Tertiarybutylphosphine. Japanese Journal of Applied Physics, 2003, 42, 2230-2236.	0.8	4
83	Properties of a GaAs Single Electron Path Switching Node Device Using a Single Quantum Dot for Hexagonal BDD Quantum Circuits. Journal of Physics: Conference Series, 2006, 38, 104-107.	0.3	4
84	Characterization of Low-Frequency Noise in GaAs Nanowire Field-Effect Transistors Controlled by Schottky Wrap Gate. Japanese Journal of Applied Physics, 2011, 50, 06GF18.	0.8	4
85	Detection of discrete surface charge dynamics in GaAs-based nanowire through metal-tip-induced current fluctuation. Japanese Journal of Applied Physics, 2016, 55, 02BD01.	0.8	4
86	Amoeba-Inspired Electronic Solution-Searching System and Its Application to Finding Walking Maneuver of a Multi-legged Robot. , 2018, , .		4
87	Resource-saving FPGA Implementation of the Satisfiability Problem Solver: AmoebaSATslim. , 2021, , .		4
88	Electrochemical formation and characterization of Schottky in-plane and wrap gate structures for realization of GaAs- and InP-based quantum wires and dots. Applied Surface Science, 1998, 123-124, 335-338.	3.1	3
89	Computer Simulation and Experimental Characterization of Single Electron Transistors Based on Schottky Wrap Gate Control of 2DEG. Japanese Journal of Applied Physics, 1998, 37, 1584-1590.	0.8	3
90	Embedded Nanowire Network Growth and Node Device Fabrication for GaAs-Based High-Density Hexagonal Binary Decision Diagram Quantum Circuits. Japanese Journal of Applied Physics, 2006, 45, 3614-3620.	0.8	3

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91	Calculating relaxation time distribution function from power spectrum based on inverse integral transformation method. Physics Letters, Section A: General, Atomic and Solid State Physics, 2015, 379, 738-742.	0.9	3
92	Fabrication and Characterization of Fully Transparent ZnO Thin-Film Transistors and Self-Switching Nano-Diodes. Journal of Physics: Conference Series, 2015, 647, 012068.	0.3	3
93	Detection of charge dynamics of a tetraphenylporphyrin particle using GaAs-based nanowire enhanced by particleâ€“metal tip capacitive coupling. Japanese Journal of Applied Physics, 2017, 56, 06GK02.	0.8	3
94	Conductance oscillation characteristics of GaAs Schottky wrap-gate single-electron transistors. Physica B: Condensed Matter, 1999, 272, 88-91.	1.3	2
95	Optimization and Interface Characterization of a Novel Oxide-Free Insulated Gate Structure for InP Having an Ultrathin Silicon Interface Control Layer. Japanese Journal of Applied Physics, 2002, 41, 1062-1066.	0.8	2
96	IIIâ€“V quantum devices and circuits based on nanoscale Schottky gate control of hexagonal quantum wire networks. Applied Surface Science, 2002, 190, 176-183.	3.1	2
97	Gated photoluminescence study of oxide-free InP MIS structure having an ultrathin silicon interface control layer. Applied Surface Science, 2002, 190, 298-301.	3.1	2
98	Interdigital-Gated HEMT Structure for High Frequency Devices. , 2006, , .		2
99	Novel Nanowire-Based Flip-Flop Circuit Utilizing Gate-Controlled GaAs Three-Branch Nanowire Junctions. Japanese Journal of Applied Physics, 2011, 50, 06GF03.	0.8	2
100	Design of nanoelectronic ICs: Noise-tolerant logic based on cyclic BDD. , 2012, , .		2
101	Identification of Graphene Layer Numbers from Color Combination Contrast Image for Wide-Area Characterization. Japanese Journal of Applied Physics, 2012, 51, 06FD09.	0.8	2
102	Characterization of GaAs-Based Three-Branch Nanowire Junction Devices by Light-Induced Local Conductance Modulation Method. Japanese Journal of Applied Physics, 2013, 52, 06GE08.	0.8	2
103	Robust myoelectric signal detection based on stochastic resonance using multiple-surface-electrode array made of carbon nanotube composite paper. Japanese Journal of Applied Physics, 2016, 55, 04EM07.	0.8	2
104	Formation and characterization of charge coupled structure of polyoxometalate particles and a GaAs-based nanowire for readout of molecular charge states. Japanese Journal of Applied Physics, 2019, 58, SDDE13.	0.8	2
105	Removal of Side-gating Effects in GaAs Quantum Nanodevices with Nano-Schottky Gates by Surface Passivation Using Si Interface Control Layer. E-Journal of Surface Science and Nanotechnology, 2005, 3, 332-337.	0.1	2
106	Surface passivation of epitaxial multilayer structures for InP-based high-speed devices by an ultrathin silicon layer. Electronics and Communications in Japan, 2002, 85, 17-28.	0.2	1
107	Control of morphology and wire width in InGaAs ridge quantum wires grown by atomic hydrogen-assisted selective molecular beam epitaxy. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1185-1189.	1.3	1
108	Terahertz response of Schottky wrap gate-controlled quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1329-1332.	0.8	1

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109	Sensing terahertz signals with III-V quantum nanostructures. , 2003, 4999, 96.		1
110	Stochastic resonance in nanodevice parallel systems. , 2009, , .		1
111	Stochastic resonance and related phenomena in nonlinear electron nanodevices. , 2014, , .		1
112	Analysis on Non-Ideal Nonlinear Characteristics of Graphene-Based Three-Branch Nano-Junction Device. IEICE Transactions on Electronics, 2015, E98.C, 434-438.	0.3	1
113	Analytical derivation of charge relaxation time distribution in transistor from current noise spectrum using inverse integral transformation method. Applied Physics Express, 2018, 11, 031201.	1.1	1
114	Fabrication and characterization of a nano-convex-embedded Si MOSFET for nano-scale electrical discrimination. Japanese Journal of Applied Physics, 2021, 60, SCCE10.	0.8	1
115	Effect of feedback delays on solution quality in amoeba-inspired computing system that solves traveling salesman problem. Applied Physics Express, 2020, 13, 114501.	1.1	1
116	Detection and Control of Charge State in Single Molecules Toward Informatics in Molecule Networks. Advances in Atom and Single Molecule Machines, 2017, , 69-94.	0.0	1
117	Current timer switch in a GaAs-based nanowire coupled with polyoxometalate nanoparticle and conductive AFM tip. Japanese Journal of Applied Physics, 2020, 59, 105005.	0.8	1
118	Chemical and Electrochemical Nanofabrication Processes for Schottky In-Plane Gate GaAs Single and Coupled Quantum Wire Transistors. Japanese Journal of Applied Physics, 2000, 39, 4651-4652.	0.8	0
119	Surface-induced large side-gating phenomenon in GaAs quantum wire transistors and its removal by surface passivation using Si interface control layer. Applied Physics Letters, 2007, 90, 132124.	1.5	0
120	Enhanced charge storage characteristics of silicon nanocrystals fabricated by electron-beam coevaporation of Si and SiOx(x=1â€‚orâ€‚2). Journal of Vacuum Science & Technology B, 2009, 27, 2462-2467.	1.3	0
121	Odd Harmonic Responses in Two-Dimensional AlGaAsâˆ•GaAs HEMT Devices Due to Plasma Wave Interaction. , 2009, , .		0
122	Analysis of Interactions between Drifting Plasma Waves in 2DEG Semiconductors and Electromagnetic Space Harmonic Waves using Three-Dimensional Transverse Magnetic Mode Method. , 2009, , .		0
123	Multi-path Switching Device Utilizing a Multi-terminal Nanowire Junction for MDD-Based Logic Circuit. , 2009, , .		0
124	Stochastic resonance nanodevices toward fluctuation-cooperative nanoelectronics. , 2010, , .		0
125	Harmonic Responses in 2DEG AlGaAsâˆ•GaAs HEMT Devices Due to Plasma Wave Interaction. , 2010, , .		0
126	Design, Fabrication and Characterization of GaAs-Based Interdigital-Gated HEMT Devices for Solid-State THz Wave Amplifiers. , 2011, , .		0

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127	Formation of silicon nanocrystals embedded in high-Îº dielectric HfO2 and their application for charge storage. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 021018.	0.6	0
128	WPG-Controlled Quantum BDD Circuits with BDD Architecture on GaAs-Based Hexagonal Nanowire Network Structure. Journal of Nanomaterials, 2012, 2012, 1-6.	1.5	0
129	Fabrication and transport performance of three-branch junction graphene nanostructure. , 2012, , .		0
130	Graphene layer number determination from red-, green-, and blue-channel of optical images. , 2012, , .		0
131	Noise-Tolerant Model of a Ternary Inverter Based on Markov Random Field. , 2013, , .		0
132	Surface dependence of nonlinear characteristic in GaAs-based three-branch nanowire junctions. , 2014, , .		0
133	Fabrication and characterization of a multiple gate nanowire FET for detecting spatially distributed molecular charges. , 2016, , .		0
134	Physarum-Inspired Electronic and Nanoelectronic Computing Systems. Emergence, Complexity and Computation, 2016, , 109-132.	0.2	0
135	Implementation of a noise-coexistence threshold logic architecture on a GaAs-based nanowire FET network. International Journal of Parallel, Emergent and Distributed Systems, 2017, 32, 287-294.	0.7	0
136	Effect of asymmetric deformation dynamics in amoeboid organism on its search ability. Bioinspiration and Biomimetics, 2021, 16, 036003.	1.5	0
137	TOWARD ULTRA-LOW POWER III-V QUANTUM LARGE SCALE INTEGRATED CIRCUITS FOR UBIQUITOUS NETWORK ERA. , 2006, , .		0
138	Harmonic Responses In 2DEG AlGaAs/GaAs HEMT Devices Due To Plasma Wave Interactions. Jurnal Teknologi (Sciences and Engineering), 0, , .	0.3	0
139	Terahertz Response in Schottky Warp-Gate Controlled Single Electron Transistors. Lecture Notes in Nanoscale Science and Technology, 2013, , 351-360.	0.4	0
140	Boolean Logic Circuits on Nanowire Networks and Related Technologies. Nano-optics and Nanophotonics, 2014, , 115-143.	0.2	0
141	Barrier Height Control and Current Transport in GaAs and InP Schottky Diodes Having An Ultrathin Silicon Interface Control Layer. , 1994, , 187-192.		0
142	Investigation on Stochastic Resonance in Quantum Dot and its Summing Network. , 0, , 140-148.		0